

Notice of References Cited	Application/Control No. 10/728,517	Applicant(s)/Patent Under Reexamination KIM ET AL.	
	Examiner Toniae M. Thomas	Art Unit 2822	Page 1 of 1

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	C	US-6,140,233	10-2000	Kwag et al.	438/669
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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